

U.S: DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

EST FOR CONTINUED EXAMINATION (RCE)

TRANSMITTAL FORM (37 C.F.R. § 1.114)

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DOCKET NO. 10191/955	APPLICAT 09/238,262	APPLICATION SERIAL N 09/238,262		KAMINER K. Alanko	A 174	RT UNIT	7700				
INVENTOR(S): Joerg SCHAEFER, Peter LINKE, Albrecht SCHWILLE, Helmut BAUMANN Thereby carlify that this correspondence is being deposited with the											
Address to: Commissioner for Patents Washington D.C. 20231 Attention: Box RCE Linearly certify that this correspondence is using the an appelopment of the patents of th											
This is a request for continued examination under 37 C.F.R. § 1.114 (RCE) of pending application Serial No.09/238,262, filed on January 27, 1999, entitled METHOD OF PRODUCING STRUCTURED WAFERS.											
The following constitute the submission required by 37 C.F.R. § 1.114(a) and is attached: X Amendment After Final Office Action originally mailed December 6, 2002. Information Disclosure Statement 02/06/2003 EAREGAYI 00000122 110600 09238262 Drawing Changes 01 FC:1801 750.00 CH Other Submission:											
1. The filing fee for this RCE and the required amendment/submission is calculated below. The fee below is calculated based on the status of the claims after the entry of the attached amendment/submission. The fee for any new additional claims is included with this RCE, the fee for previously entered additional claims having already been paid.											
	CLAIMS REMAINING AFTER AMENDMENT	MINUS	HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT NUMBER EXTRA	RATE (\$) PER CLAIM	FEE	(\$)				

	CLAIMS REMAINING AFTER AMENDMENT	MINUS	HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT NUMBER EXTRA	RATE (\$) PER CLAIM	FEE (\$)
BASIC FEE		4.1	4 3	1. 10.		750.00
TOTAL CLAIMS	11 .	20	20	0	18.00	0.00
INDEPENDENT CLAIMS	1	3	3	0	84.00	0.00
MULTIPLE DEPENDENT CLAIM					280.00	
		H Sign		*Number extra must be zero or larger	TOTAL	750.00
	If Applicant is a small entity und and 1.27, then divide total fee by		S	MALL ENTITY TOTAL	0.00	

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- 2. Please charge the required RCE and submission filing fee of \$750.00 to the deposit account of Kenyon & Kenyon, deposit account number 11-0600.
- 3. Applicants request a one month extension of time to respond to the Office Action mailed September 30, 2002, resetting the response date to January 30, 2003. The extension fee of \$110.00 should be charged to the deposit account of **Kenyon & Kenyon**, deposit account number 11-0600.
- 4. The Commissioner is hereby authorized to charge payment of fees, including any additional fees required, associated with this communication or arising during the pendency of this application, or to credit any overpayment, to the deposit account of **Kenyon & Kenyon**, deposit account number 11-0600.
- 5. A duplicate copy of this transmittal form is enclosed.

1/30/03

Respectfully submitted,

Richard L. Mayer, Reg. No. 22,490

26646

PATENT TRADEMARK OFFICE
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[10191/95

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

entor(s)

Joerg SCHAEFER et al.

Serial No.

09/238,262

Filed

January 27, 1999

For

METHOD OF PRODUCING STRUCTURED WAFERS

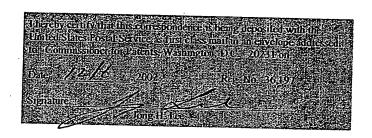
Examiner

Anita Karen Alanko

Art Unit

1746

*Commissioner for Patents Washington, D.C. 20231



AMENDMENT AFTER FINAL OFFICE ACTION

SIR:

In response to the Final Office Action dated September 30, 2002, kindly amend the above-identified application as set forth below. Entry of the amendment is requested since it raises no new issues and puts the claims in condition for allowance and/or in better form for appeal.

IN THE CLAIMS:

Kindly amend claim 14 as follows:

(Amended) A method of etching a wafer, comprising the 14. steps of:

providing a wafer having a surface and edge areas; dividing the surface of the wafer into positive areas and negative areas, the negative areas including the edge areas of the wafer;

providing the negative areas with a first passivation layer to protect the negative areas from a subsequent second etching process;

providing at least one δt the positive areas with a

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